

Title (en)
METHODS OF FORMING SEMICONDUCTOR DEVICE HAVING A SELF-ALIGNED CONTACT STRUCTURE

Title (de)
HERSTELLUNGSVERFAHREN FÜR HALBLEITERBAUELEMENT MIT SELBSTJUSTIERTER KONTAKTSTRUKTUR

Title (fr)
PROCEDES DE FABRICATION D'UN DISPOSITIF SEMI-CONDUCTEUR COMPRENANT UNE STRUCTURE A CONTACTS AUTOALIGNES

Publication
EP 1169731 B1 20090225 (EN)

Application
EP 00983523 A 20001208

Priority

- KR 0001422 W 20001208
- KR 19990055862 A 19991208
- KR 20000003249 A 20000124
- KR 20000043125 A 20000726

Abstract (en)
[origin: WO0143176A1] A self-aligned contact structure in a semiconductor device and methods for making such contact structure wherein the semiconductor device has a semiconductor substrate having active regions, an interlayer insulating layer covering the semiconductor substrate excluding at least a portion of each active region, at least two parallel interconnections on the interlayer insulating layer, at least one active region being relatively disposed between the at least two parallel interconnections, each interconnection having sidewalls, bottom and a width (x), a mask pattern having a top portion (z) and a bottom portion (y) formed on each interconnection, and a conductive layer pattern penetrating at least a portion of the interlayer insulating layer between the mask pattern and being electrically connected to at least one active region, wherein: $x \leq y \leq z$ and $x < z$. A second interlayer insulating layer having a relatively low dielectric constant is interposed between the conductive layer and the interconnections, which reduces the parasitic capacitance therebetween.

IPC 8 full level
H01L 21/28 (2006.01); **H01L 21/60** (2006.01); **H01L 21/768** (2006.01); **H10B 12/00** (2023.01)

CPC (source: EP US)
H01L 21/76834 (2013.01 - EP); **H01L 21/76895** (2013.01 - US); **H01L 21/76897** (2013.01 - EP US); **H10B 12/0335** (2023.02 - EP US); **H10B 12/482** (2023.02 - EP US)

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
WO 0143176 A1 20010614; CN 1148788 C 20040505; CN 1339172 A 20020306; DE 60041638 D1 20090409; EP 1169731 A1 20020109; EP 1169731 A4 20060118; EP 1169731 B1 20090225; EP 2053638 A2 20090429; EP 2053638 A3 20090729; JP 2003516632 A 20030513; JP 4382321 B2 20091209; US 2003127677 A1 20030710; US 6534813 B1 20030318; US 6720269 B2 20040413

DOCDB simple family (application)
KR 0001422 W 20001208; CN 00803522 A 20001208; DE 60041638 T 20001208; EP 00983523 A 20001208; EP 09150301 A 20001208; JP 2001543767 A 20001208; US 34721903 A 20030121; US 88958801 A 20010802